Q1
(a) Due to the fact that
Silicon is aloped with As
we also know that Asis +5"
Value in Semiconductors

> When doped with Silicon,
There exists many electrons

Thus, the material is

1 — type

(b)  $Ni = PT^{\frac{3}{2}} e^{\frac{-Eg}{2kT}}$   $= (5.23 \times 10^{13})(300)^{\frac{3}{2}} e^{\frac{-1.1}{2(86 \times 10^{4})(300)}}$   $= 1.5 \times 10^{10} \text{ cm}^{\frac{3}{2}}$   $Nole = 1 \text{ electron} = 5 \times 10^{16} \text{ cm}^{\frac{3}{2}}$   $= \frac{1.5 \times 10^{16} \text{ cm}^{\frac{3}{2}}}{100}$   $= \frac{1.5 \times 10^{16} \text{ cm}^{\frac{3}{2}}}{100}$   $= \frac{1.5 \times 10^{3} \text{ cm}^{\frac{3}{2}}}{100}$   $= \frac{2.25 \times 10^{3} \text{ cm}^{\frac{3}{2}}}{100}$   $= \frac{1.5 \times 10^{3} \text{ cm}^{\frac{3}{2}}}{1$ 

(C)  $Ni = \beta T^{\frac{3}{2}} e^{\frac{-Eq}{2kT}}$ =  $(5.23 \times 10^{15}) (350)^{\frac{3}{2}} \cdot e^{\frac{-1.1}{2(86 \times 10^{6}) \cdot 350}}$ =  $3.97 \times 10^{10} \text{ cm}^{\frac{3}{2}}$   $Nd = \text{Nelectron} = 5 \times 10^{16} \text{ cm}^{\frac{3}{2}}$   $No = \text{n hole} = \frac{\text{n} \cdot 2^{-1}}{\text{nd}}$ =  $(3.97)^{\frac{3}{2}} \times 10^{\frac{3}{2}} \text{ cm}^{\frac{3}{2}}$ =  $3.15 \times 10^{3} \text{ cm}^{\frac{3}{2}}$   $\Rightarrow \text{In Summary electron} \cdot 5 \times 10^{6} \text{ cm}^{\frac{3}{2}}$  $\text{hole} : 3.15 \times 10^{3} \text{ cm}^{\frac{3}{2}}$ 

$$I_{2} = I_{1} - I_{1}$$

$$I_{1} = \frac{V_{1} - V_{2}}{P_{1}}$$

$$I_{1} = \frac{V_{2} - V_{2}}{P_{1}}$$

$$I_{2} = \frac{V_{1} - V_{2}}{P_{1}} - \frac{V_{2}}{P_{1}}$$

$$I_{3} = \frac{V_{2} - V_{2}}{220} - \frac{10}{380}$$

$$I_{3} = \frac{1}{22} - \frac{1}{38}$$

$$(C1 \text{ From (b)})$$

$$\Rightarrow J_8 = \frac{V_I - V_B}{P_I} \frac{U_B}{P_I}$$

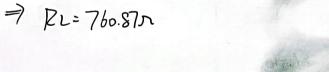
$$\Rightarrow J_8 = \frac{10}{175} - \frac{10}{P_I}$$

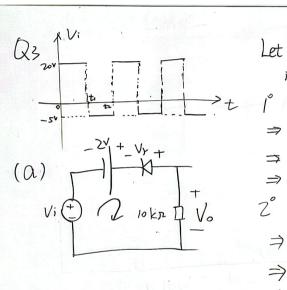
$$72(max) = V_2 \cdot I_2$$

$$V_2 = 10 \text{ V}$$

$$72(-0x) = (40 \text{ mW})$$

(a) Apply kelto node 
$$A \Rightarrow IZ = \frac{4}{203}A = 19.4 \text{ mA}$$
  $\Rightarrow 44 \text{ mW} = \frac{1}{22} - \frac{10}{\text{Pl}}$   
 $\Rightarrow I_z = I_{z} + I_{z}$   $\Rightarrow I_{z} = \frac{4}{203}A = 26.32 \text{ mA} \Rightarrow P_{z} = 6875 \text{ n}$   
 $\Rightarrow I_z = I_{z} - I_{z}$ 





Let us analyze the situation
in a period (ontz)

I' When atta

Diode is cut-off

iD = 0

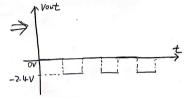
>> V0=iD·10 km=0 V

2° when ti<t stz

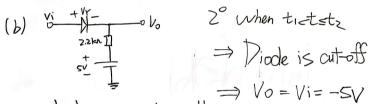
→ Piode is on.

⇒ Apply kul to this loop

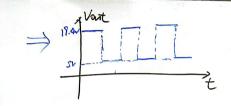
=> 2+ Vr -Vo+Vi=0



P When 0≤t≤ti ⇒Diode is on ⇒Va=Vi-Vr=19.4V



Let us analyze the situation in a period (out)





Q4

$$V_1 = V_2 + V_3 + V_4$$
 $V_2 = V_3 + V_4$ 
 $V_3 = V_4 + V_5$ 
 $V_4 = V_5 + V_6$ 
 $V_6 = V_7 + V_8$ 
 $V_7 = V_7 + V_8$ 
 $V_8 = V_8 + V_8$ 
 $V_9 = V_9 + V_9$ 
 $V$ 

AB path is open

$$\Rightarrow Vo = Vr + IDz \cdot Oskn$$

$$\Rightarrow Vo = 1.07V$$

$$\Rightarrow In Summary$$

$$\begin{cases} Vo = 1.07V \\ ID = 0.4 \\ IDz = 0.94mA \end{cases}$$

$$V_1 = V_2 = OV$$

$$V_1 = V_2 = OV$$

$$V_1 = IoV$$

$$V_2 = IoV$$

$$V_3 = IoV$$

$$V_4 = IoV$$

$$V_5 = IoV$$

$$V_7 = IoV$$

$$V_8 = IoV$$

$$V_9 =$$



Q5
$$\frac{+\sqrt{r}}{\sqrt{r}}$$

$$\frac{2}{\sqrt{r}}$$

$$\frac{1}{\sqrt{r}}$$

(b) From (C)

$$\Rightarrow |t| = \frac{4e^{2ST}}{|g_0| 12e^{-1}} = |.8| ms$$

$$tz = \frac{139.717}{|g_0| 72e^{-1}} = 647 ms$$

$$\Rightarrow st = 4.6 ms$$

$$|tt| = \frac{Vs.97}{2}$$

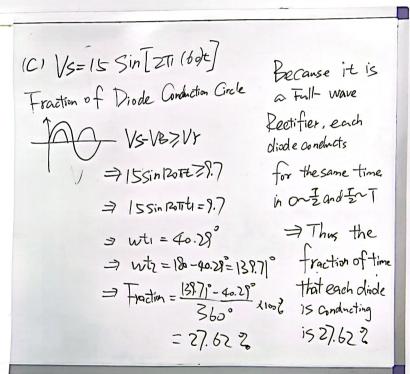
$$\Leftrightarrow = \int_{t.3}^{t.1} itt$$

$$\Rightarrow R = \int_{t.3}^{t.1} itt$$

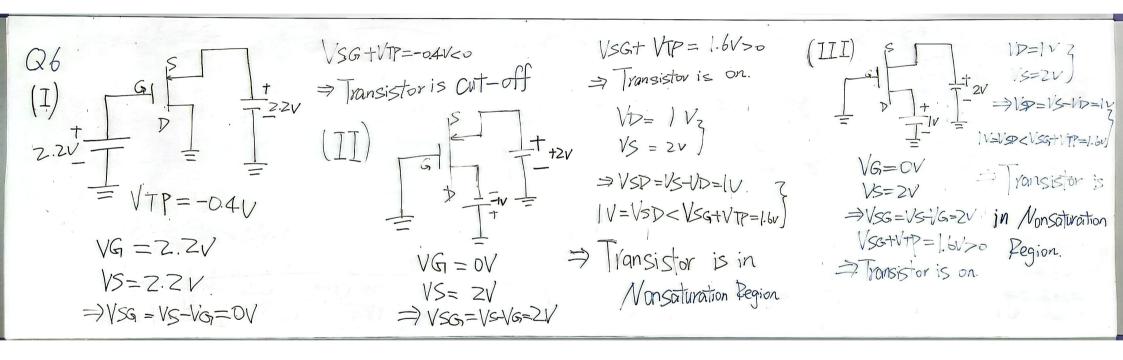
$$\Rightarrow R = [.3] \int_{t.2}^{t.2} \frac{15sin 12sT-1.7}{442}$$

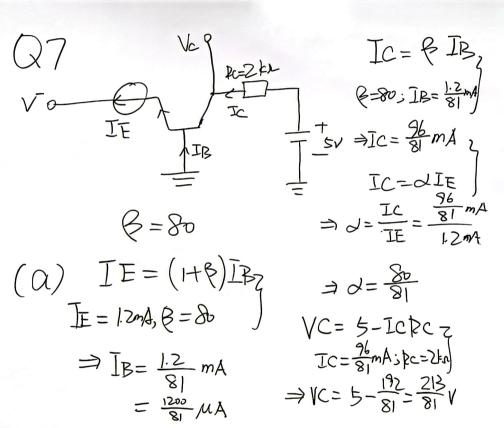
$$\Rightarrow I = [.8] \int_{t.2}^{t.2} \frac{15sin 12sT-1.7}{442}$$

$$\Rightarrow$$









In Summary IC = 
$$\frac{1}{8}$$
 In Summary

$$\begin{array}{l}
IR = \frac{1}{87} MA + \frac{1}{8} MA \\
P = 80; IR = \frac{28}{81} MA
\end{array}$$

$$\begin{array}{l}
IR = \frac{1}{87} MA + \frac{1}{8} MA
\end{array}$$

$$\begin{array}{l}
IR = \frac{800}{81} MA = \frac{9}{8} MA
\end{array}$$

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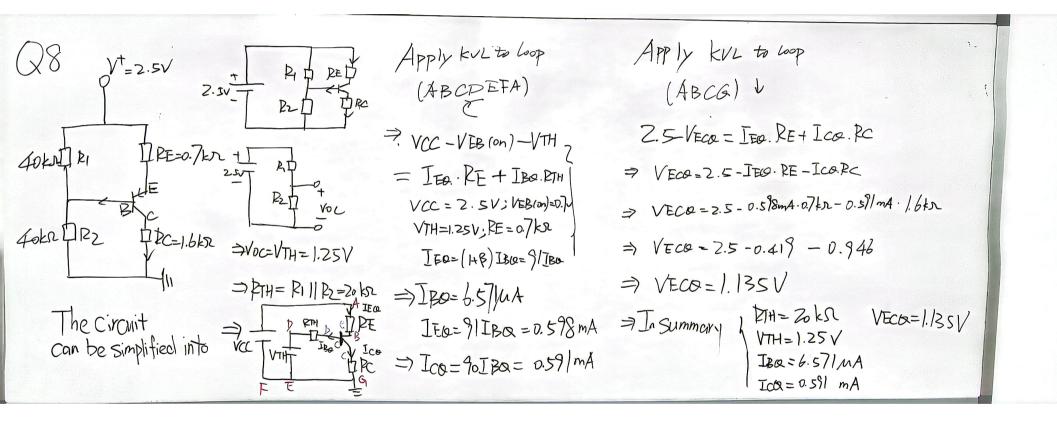
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$$\begin{array}{l}
IR = \frac{800}{10} MA = \frac{9}{8} MA$$

$$\begin{array}{l}
IR = \frac{1}{8} MA = \frac{1}{10}$$



Apply kulto loop 08 (b) From. (a) (ABCDEFA) = the circuit can be simplified into => VCC -VEBron)-VTH = IEQ. PE+ IBQ. PTH VCC=2.5v; VEB(on)=0.74 RIH VTH=123V; RE=0.7km IE=(1+B)IBO=151IBO => 180= 4.375MA Despite the change of B IEQ = 0.661 mA > ,VTH keeps 1.25V as (a) ⇒ Ica= 0.656 mA 2TH keeps. 20 ks. as (a)

Apply KUL to LOOP (ABCG) L

=> 2.5 - VECO = IEO. PE+ I CO. PC

=> VECQ = Z.S-IEO.RE - ICO.RC

=> VECQ = 0.988 V In Summary

8	Ica	VECO
90	0.591 mA	1./35V
150	0. bsbmA	v.988v
42	0.626-0.49/ 0.626-0.49/	Scorx 281.1-889.0
Result	=+10.982	= -12.9526